# Low-power radio design for the IoT Exercise 5 (25.03.2021)

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#### Problem 1 Common Source Analysis

The circuit in the Figure below is a single MOSFET Common Source (CS) Amplifier.



Figure 1: Common Source Amplifier.

- Draw the small-signal equivalent circuit of the CS. Consider the bias current source to be ideal. (*Hint*: split the gate capacitance,  $C_G$ , into the intrinsic and the extrinsic parts,  $C_{Gi}$  and  $C_{Ge}$ , and the load capacitance,  $C_L$ , into a constant capacitance and a self-loading capacitance per unit width,  $C_{L0}$  and  $C_w$ , respectively).
- Derive the expression of the transit frequency,  $\omega_t$ , by using the small signal equivalent circuit.
- Express  $\omega_t$  in terms of the inversion coefficient, IC. (Hint: introduce the specific frequency,  $\omega_{spec} \triangleq \frac{2\mu U_T}{L^2}$ , and neglect the velocity saturation  $(\lambda_c = 0)$ ).
- Derive  $\omega_{tspec}$ , the transit frequency for  $IC = 1$  and WI.
- Derive the expression for the unity-gain frequency,  $\omega_u$ . (*Hint*: neglect the output conductance of the transistor  $(g_{ds} = 0)$ .
- Express  $\omega_u$  in terms of the normalized gain-bandwidth (GBW) for a squared transistor biased in WI,  $\omega_L \triangleq \frac{I_{spec}}{nU_{\tau}C_L}$  $\frac{r_{spec}}{nU_T C_L}$ , and the normalized source transconductance,  $g_{ms}$ .

#### Problem 2 Common Source Design

Once the self loading capacitance per unit width is taken into account, the formulas for the  $I_D$  and  $W/L$ normalized to  $\Omega \triangleq \frac{\omega_u}{\omega_L}$  are

$$
i_b \triangleq \frac{I_D}{I_{spec_{\Box}}} \cdot \frac{1}{\Omega} = \frac{IC}{g_{ms} - \Theta};
$$
  

$$
AR \triangleq \frac{W}{L} \cdot \frac{1}{\Omega} = \frac{1}{g_{ms} - \Theta},
$$
 (1)

where  $\Theta$  is equal to  $\frac{C_w L}{C_{L0}} \cdot \frac{\omega_u}{\omega_L} = \frac{\omega_u}{\omega_{tspec}}$ . Design the CS amplifier, shown in Fig. 1, for the following specifications at room temperature:

$$
f_u = 18 \text{ MHz} \quad C_{L0} = 60 \text{ fF} \quad V_{DD} = 1.8 \text{ V} \quad L = 40 \text{ nm} \quad C_w = 0.450 \text{ fF/nm}, \tag{2}
$$

and by assuming the following values for the technology parameters

$$
I_{spec\Box} = 950 \,\text{nA} \quad n = 1.5 \quad V_{T0} = 455 \,\text{mV} \quad \lambda_c = 0.4875 \quad L_{sat} = 19.5 \,\text{nm}. \tag{3}
$$

- Find the  $IC_{opt}$ , the value of the inversion coefficient for which the bias current is minimum. Assume no velocity saturation.
- Based on the  $IC_{opt}$ , find the values of the bias current,  $I_q$ , and the transistor aspect ratio,  $W/L$ , to achieve the specified gian-bandwidth,  $w_u$ .

# Solutions to Exercise 5 (25.03.2021)

### Problem 1 Common Source Analysis

Draw the small-signal equivalent circuit of the CS.



Figure 1: Common Source Amplifier Small Signal Equivalent Circuit.

where

$$
C_G \triangleq C_{Gi} + C_{Ge};
$$
  
\n
$$
C_L \triangleq C_{L0} + C_w \cdot W.
$$
\n(1)

Derive the expression of the transit frequency,  $\omega_t$ , by using the small signal equivalent circuit.



Figure 2: Small Signal Equivalent Circuit to derive  $\omega_t$ .

So,

$$
\Delta I_{in} = sC_G V_G; \n\Delta I_{out} = G_m V_G,
$$
\n(2)

which leads to

$$
\frac{\Delta I_{out}}{\Delta I_{in}} = \frac{G_m}{sC_G}.\tag{3}
$$

By imposing  $\left|\frac{\Delta I_{out}}{\Delta I_{in}}\right|=1$ , we have

$$
\omega_t = \frac{G_m}{C_G}.\tag{4}
$$

Express  $\omega_t$  in terms of the inversion coefficient, IC.

The term  $G_m$  can be written as

$$
G_m = \frac{G_{ms}}{n} = \frac{G_{spec}}{n}g_{ms}.\tag{5}
$$

while  $C_G$  is

$$
C_G = C_{Gi} + C_{Ge} = W \cdot L \cdot C_{ox} \left( c_{Gi} + \frac{C_{Ge}}{W \cdot L \cdot C_{ox}} \right),\tag{6}
$$

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hence

$$
\omega_t = \frac{\frac{G_{spec}}{n}}{W \cdot L \cdot C_{ox}} \cdot \frac{g_{ms}}{\left(c_{Gi} + \frac{C_{Ge}}{W \cdot L \cdot C_{ox}}\right)}.\tag{7}
$$

Since  $G_{spec} = \frac{I_{spec}}{U_{Tr}}$  $\frac{\partial^{pec} \Box}{\partial T} \cdot \frac{W}{L}$  and  $I_{spec \Box} = 2n\mu C_{ox} U_T^2$ , we obtain begine quation

$$
\frac{\frac{G_{spec}}{n}}{W \cdot L \cdot C_{ox}} = \frac{2\mu U_T}{L^2} = \omega_{spec},\tag{8}
$$

and so

$$
\omega_t = \omega_{spec} \cdot \frac{g_{ms}}{c_{Gi} + \frac{C_{Ge}}{W \cdot L \cdot C_{ox}}}.\tag{9}
$$

By replacing  $g_{ms}$  we obtain

$$
\omega_t = \omega_{spec} \cdot \frac{\frac{1}{2}(\sqrt{4IC + 1} - 1)}{c_{Gi} + \frac{C_{Ge}}{W \cdot L \cdot C_{ox}}}. \tag{10}
$$

• Derive  $\omega_{tspec}$ , the transit frequency for  $IC = 1$  and WI.

For bias in WI

$$
g_{ms} = IC,\tag{11}
$$

hence, for  $IC = 1$  we have

$$
\omega_{tspec} = \frac{\omega_{spec}}{c_{Gi} + \frac{C_{Ge}}{W \cdot L \cdot C_{ox}}}.\tag{12}
$$

• Derive the expression for the unity-gain frequency,  $\omega_u$ .

For the CS in Fig. 1, we have

$$
A_v = \frac{\Delta V_{out}}{\Delta V_{in}} = -\frac{G_m}{sC_L}.\tag{13}
$$

By imposing  $|A_v| = 1$ , we obtain  $\omega_u$ 

$$
\omega_u = \frac{G_m}{C_L}.\tag{14}
$$

Express  $\omega_u$  in terms of the normalized gain-bandwidth (GBW) for a squared transistor biased in WI,  $\omega_L \triangleq \frac{I_{spec}}{nU_{TC}}$  $\frac{r_{spec}}{nU_T C_L}$ , and the normalized source transconductance,  $g_{ms}$ .

$$
\omega_u = \frac{G_m}{C_L} = \frac{I_{spec_{\Box}}}{nU_T C_L} \cdot \frac{W}{L} \cdot g_{ms} = \omega_L \cdot \frac{W}{L} \cdot g_{ms}.
$$
\n(15)

## Problem 2 Common Source Design

Find the  $IC_{opt}$ , the value of the inversion coefficient for which the bias current is minimum. Assume no velocity saturation.

$$
\Theta = \frac{C_w L}{C_{L0}} \cdot \frac{\omega_u}{\omega_L} = \frac{0.450 \,\text{ffmm}^{-1} \cdot 40 \,\text{nm}}{60 \,\text{ff}} \cdot \frac{2\pi \cdot 18 \,\text{MHz}}{1.5 \cdot 26 \,\text{mV} \cdot (60 \,\text{ff} + 0.450 \,\text{ff/nm} \cdot 40 \,\text{nm})} = 0.1086 \tag{16}
$$

Hence,

$$
IC_{opt} \cong 2\Theta + sqrt(\Theta) = 0.547
$$
\n<sup>(17)</sup>

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Based on the  $IC_{opt}$ , find the values of the bias current,  $I_q$ , and the transistor aspect ratio,  $W/L$ , to achieve the specified gian-bandwidth,  $w_u$ .

By using the formula reported in the text, we obtain

$$
i_b = \frac{0.547}{0.3927 - 0.1086} = 1.98254;
$$
  

$$
AR = \frac{1}{0.3927 - 0.1086} = 3.5205,
$$
 (18)

and finally

$$
I_q = i_b \cdot I_{spec\Box} \cdot \frac{\omega_u}{\omega_L} = 662 \text{ nA};
$$
  
\n
$$
\frac{W}{L} = AR \cdot \frac{\omega_u}{\omega_L} = 1.275 \rightarrow W = 51 \text{ nm}.
$$
\n(19)